



PSMN013-30KL

N-channel 30 V 13 mΩ logic-level MOSFET in SO8

Rev. 01 — 14 April 2011

Objective data sheet

1. Product profile

1.1 General description

Logic level N-channel enhancement mode MOSFET in SO8 package qualified to 150 °C. This product is designed and qualified for use in a wide range of industrial, communications and power supply equipment

1.2 Features and benefits

- High efficiency due to low switching and conduction losses
- High performance replacement for legacy SO8 designs
- Suitable for logic-level gate drive
- Suitable for wave and reflow soldering

1.3 Applications

- DC-to-DC converters
- Load switching
- Portable equipment

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{DS}	drain-source voltage	$T_j \geq 25\text{ °C}$; $T_j \leq 150\text{ °C}$	-	-	30	V
I_D	drain current	$V_{GS} = 10\text{ V}$; $T_{mb} = 25\text{ °C}$; see Figure 1	-	-	12	A
P_{tot}	total power dissipation	$T_{mb} = 25\text{ °C}$; see Figure 2	-	-	3	W
T_j	junction temperature		-55	-	150	°C
Static characteristics						
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 4.5\text{ V}$; $I_D = 5\text{ A}$; $T_j = 25\text{ °C}$; see Figure 12	-	16.2	19	mΩ
		$V_{GS} = 10\text{ V}$; $I_D = 5\text{ A}$; $T_j = 25\text{ °C}$; see Figure 12	-	11.1	13	mΩ

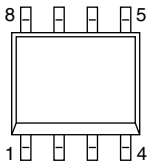
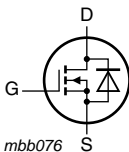


Table 1. Quick reference data ...continued

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Dynamic characteristics						
Q_{GD}	gate-drain charge	$V_{GS} = 10\text{ V}; I_D = 5\text{ A}; V_{DS} = 15\text{ V};$ see Figure 14 ; see Figure 15	-	1.9	-	nC
$Q_{G(\text{tot})}$	total gate charge	$V_{GS} = 10\text{ V}; I_D = 5\text{ A}; V_{DS} = 15\text{ V};$ see Figure 14 ; see Figure 15	-	11.7	-	nC
		$V_{GS} = 4.5\text{ V}; I_D = 5\text{ A}; V_{DS} = 15\text{ V};$ see Figure 14 ; see Figure 15	-	5.7	-	nC
Avalanche ruggedness						
$E_{DS(\text{AL})S}$	non-repetitive drain-source avalanche energy	$V_{GS} = 10\text{ V}; T_{j(\text{init})} = 25\text{ }^\circ\text{C};$ $I_D = 12\text{ A}; V_{\text{sup}} \leq 30\text{ V}; R_{GS} = 50\text{ } \Omega;$ unclamped	-	-	43	mJ

2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source	 <p>SOT96-1 (SO8)</p>	 <p>mbb076</p>
2	S	source		
3	S	source		
4	G	gate		
5	D	drain		
6	D	drain		
7	D	drain		
8	D	drain		

3. Ordering information

Table 3. Ordering information

Type number	Package		Version
	Name	Description	
PSMN013-30KL	SO8	plastic small outline package; 8 leads; body width 3.9 mm	SOT96-1

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 150 °C	-	30	V
V _{DGR}	drain-gate voltage	T _j ≥ 25 °C; T _j ≤ 150 °C; R _{GS} = 20 kΩ	-	30	V
V _{GS}	gate-source voltage		-20	20	V
I _D	drain current	V _{GS} = 10 V; T _{mb} = 25 °C; see Figure 1	-	12	A
		V _{GS} = 10 V; T _{mb} = 100 °C; see Figure 1	-	8	A
I _{DM}	peak drain current	pulsed; t _p ≤ 10 μs; T _{mb} = 25 °C; see Figure 3	-	46	A
P _{tot}	total power dissipation	T _{mb} = 25 °C; see Figure 2	-	3	W
T _{stg}	storage temperature		-55	150	°C
T _j	junction temperature		-55	150	°C
T _{sld(M)}	peak soldering temperature		-	260	°C
Source-drain diode					
I _S	source current	T _{mb} = 25 °C	-	12	A
I _{SM}	peak source current	pulsed; t _p ≤ 10 μs; T _{mb} = 25 °C	-	46	A
Avalanche ruggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	V _{GS} = 10 V; T _{j(init)} = 25 °C; I _D = 12 A; V _{sup} ≤ 30 V; R _{GS} = 50 Ω; unclamped	-	43	mJ

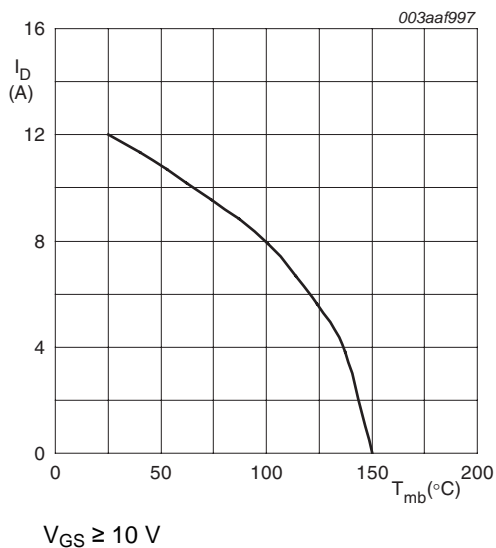
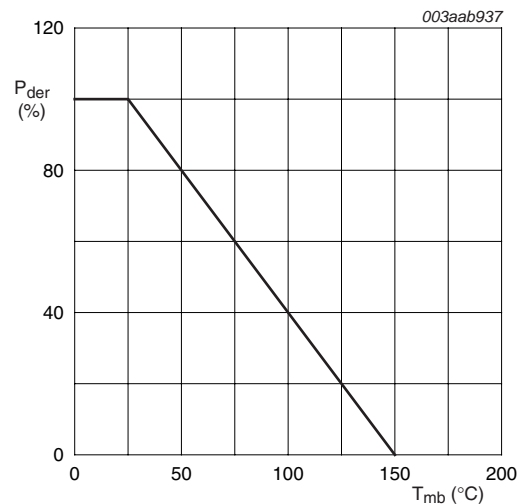
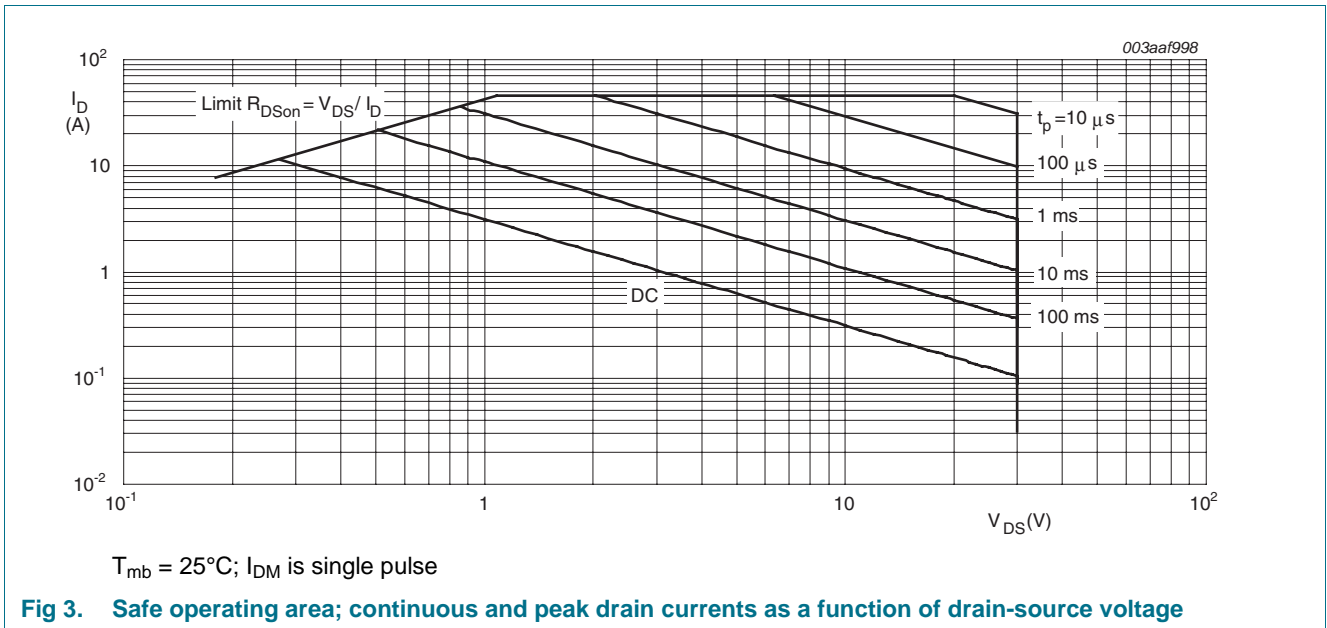


Fig 1. Continuous drain current as a function of mounting base temperature



$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

Fig 2. Normalized total power dissipation as a function of solder point temperature



5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-sp)}$	thermal resistance from junction to solder point	see Figure 4	-	30	40	K/W

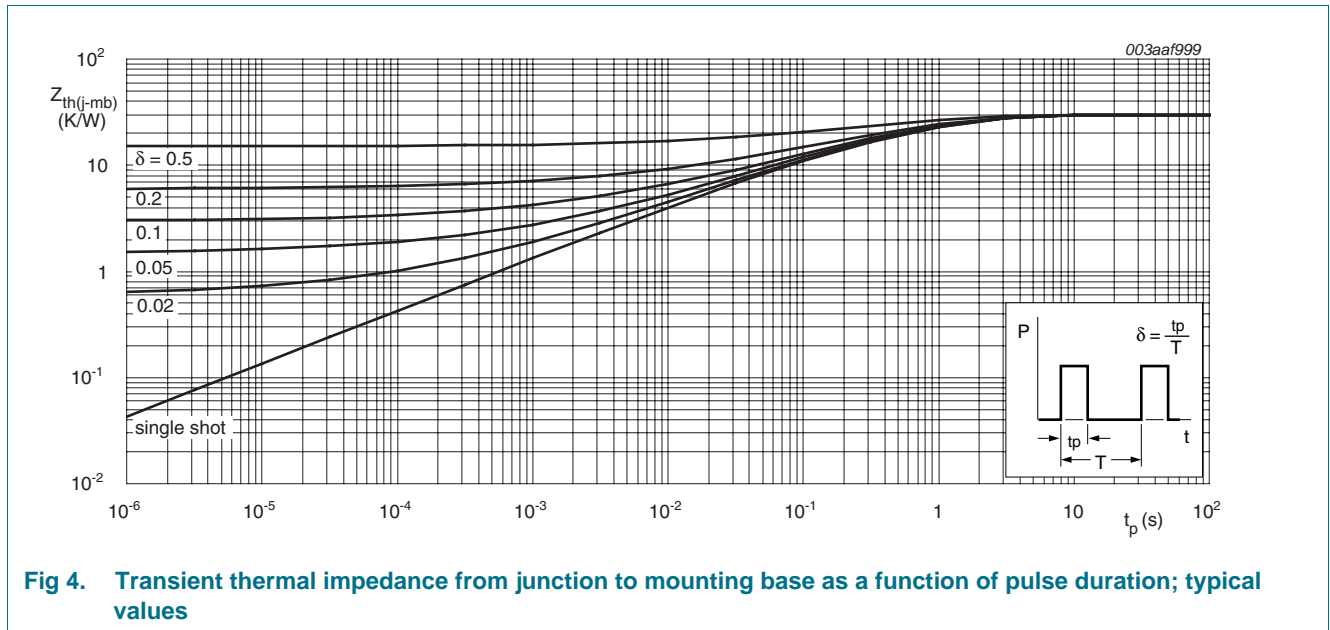


Fig 4. Transient thermal impedance from junction to mounting base as a function of pulse duration; typical values

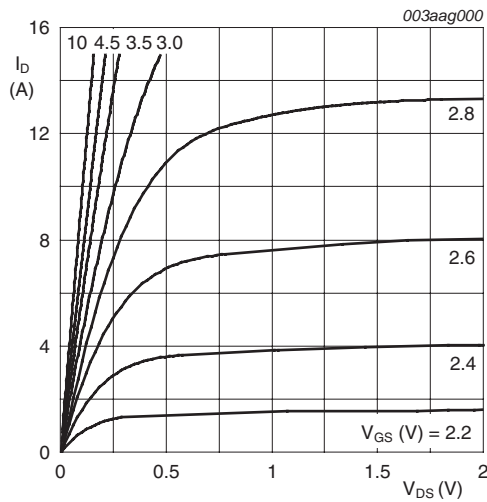
6. Characteristics

Table 6. Characteristics
Tested to JEDEC standards where applicable.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 250 \mu\text{A}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$	30	-	-	V
		$I_D = 250 \mu\text{A}; V_{GS} = 0 \text{ V}; T_j = -55 \text{ }^\circ\text{C}$	27	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ }^\circ\text{C};$ see Figure 10 ; see Figure 11	1.3	1.7	2.15	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ }^\circ\text{C};$ see Figure 11	-	-	2.55	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 150 \text{ }^\circ\text{C};$ see Figure 11	0.5	-	-	V
I_{DSS}	drain leakage current	$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$	-	0.1	1	μA
		$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 125 \text{ }^\circ\text{C}$	-	-	50	μA
I_{GSS}	gate leakage current	$V_{GS} = -20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$	-	2	100	nA
		$V_{GS} = 20 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$	-	2	100	nA
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 4.5 \text{ V}; I_D = 5 \text{ A}; T_j = 25 \text{ }^\circ\text{C};$ see Figure 12	-	16.2	19	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 5 \text{ A}; T_j = 100 \text{ }^\circ\text{C};$ see Figure 13 ; see Figure 12	-	-	17.9	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 5 \text{ A}; T_j = 150 \text{ }^\circ\text{C};$ see Figure 13 ; see Figure 12	-	19.9	23.4	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 5 \text{ A}; T_j = 25 \text{ }^\circ\text{C};$ see Figure 12	-	11.1	13	mΩ
R_G	internal gate resistance (AC)	$f = 1 \text{ MHz}$	-	1.33	-	Ω
Dynamic characteristics						
$Q_{G(tot)}$	total gate charge	$I_D = 5 \text{ A}; V_{DS} = 15 \text{ V}; V_{GS} = 10 \text{ V};$ see Figure 14 ; see Figure 15	-	11.7	-	nC
		$I_D = 5 \text{ A}; V_{DS} = 15 \text{ V}; V_{GS} = 4.5 \text{ V};$ see Figure 14 ; see Figure 15	-	5.7	-	nC
		$I_D = 0 \text{ A}; V_{DS} = 0 \text{ V}; V_{GS} = 10 \text{ V}$	-	10.5	-	nC
Q_{GS}	gate-source charge	$I_D = 5 \text{ A}; V_{DS} = 15 \text{ V}; V_{GS} = 10 \text{ V};$ see Figure 14 ; see Figure 15	-	1.5	-	nC
$Q_{GS(th)}$	pre-threshold gate-source charge		-	1.1	-	nC
$Q_{GS(th-pl)}$	post-threshold gate-source charge		-	0.4	-	nC
Q_{GD}	gate-drain charge		-	1.9	-	nC
$V_{GS(pl)}$	gate-source plateau voltage	$I_D = 5 \text{ A}; V_{DS} = 15 \text{ V};$ see Figure 14 ; see Figure 15	-	2.52	-	V
C_{iss}	input capacitance	$V_{DS} = 15 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$	-	744	-	pF
C_{oss}	output capacitance	$T_j = 25 \text{ }^\circ\text{C};$ see Figure 16	-	143	-	pF
C_{rss}	reverse transfer capacitance		-	77	-	pF

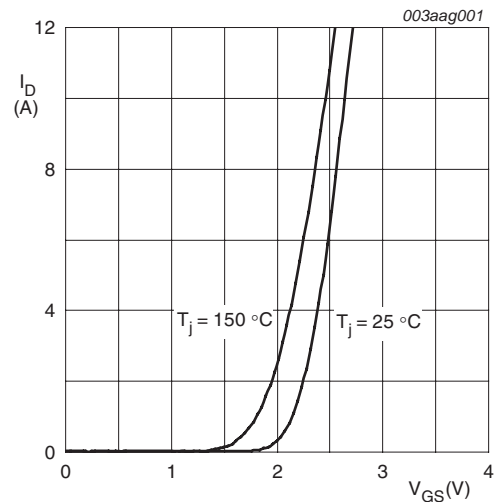
Table 6. Characteristics ...continued
 Tested to JEDEC standards where applicable.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$t_{d(on)}$	turn-on delay time	$V_{DS} = 15\text{ V}; R_L = 1\ \Omega; V_{GS} = 4.5\text{ V};$	-	5	-	ns
t_r	rise time	$R_{G(ext)} = 4.7\ \Omega; T_j = 25\text{ }^\circ\text{C}$	-	11	-	ns
$t_{d(off)}$	turn-off delay time		-	15	-	ns
t_f	fall time		-	5	-	ns
Source-drain diode						
V_{SD}	source-drain voltage	$I_S = 5\text{ A}; V_{GS} = 0\text{ V}; T_j = 25\text{ }^\circ\text{C};$ see Figure 17	-	0.81	1.2	V
t_{rr}	reverse recovery time	$I_S = 5\text{ A}; di_S/dt = 100\text{ A}/\mu\text{s};$	-	19	-	ns
Q_r	recovered charge	$V_{GS} = 0\text{ V}; V_{DS} = 15\text{ V}$	-	11	-	nC



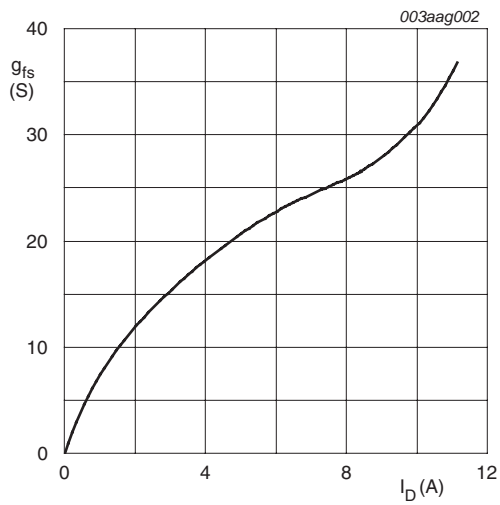
$T_j = 25^\circ\text{C}$

Fig 5. Output characteristics: drain current as a function of drain-source voltage; typical values



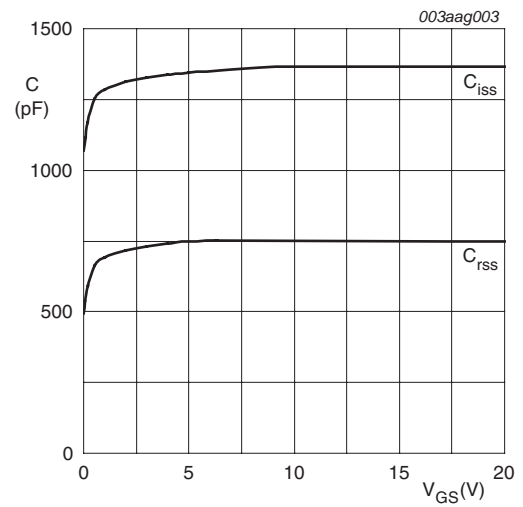
$V_{DS} = 10\text{ V}$

Fig 6. Transfer characteristics: drain current as a function of gate-source voltage; typical values



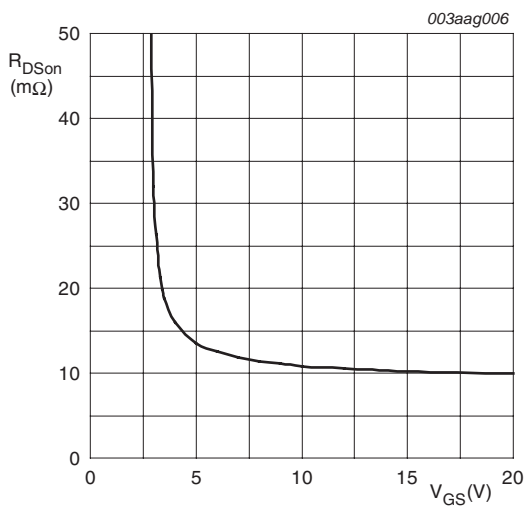
$T_j = 25^\circ\text{C}; V_{DS} = 10\text{ V}$

Fig 7. Forward transconductance as a function of drain current; typical values



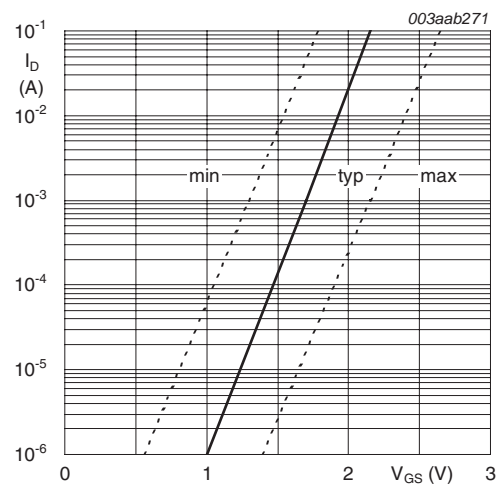
$V_{DS} = 0\text{ V}; f = 1\text{ MHz}$

Fig 8. Input and reverse transfer capacitances as a function of gate-source voltage; typical values



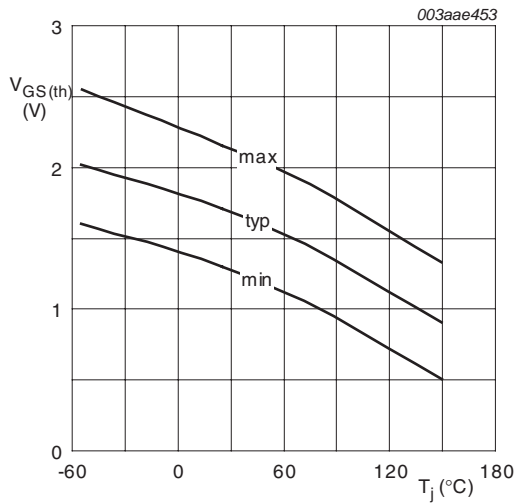
$T_j = 25^\circ\text{C}; I_D = 5\text{ A}$

Fig 9. Drain-source on-state resistance as a function of gate-source voltage; typical values



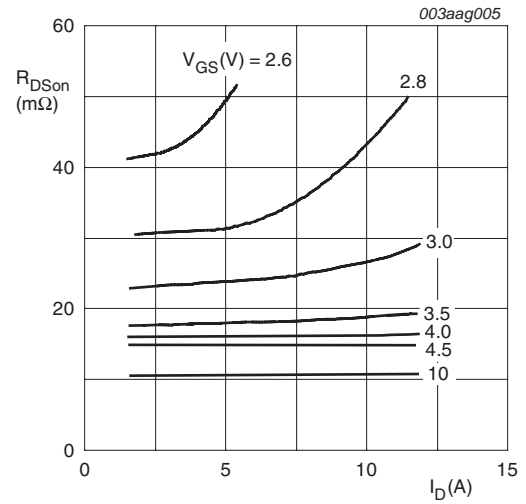
$T_j = 25^\circ\text{C}; V_{DS} = 5\text{ V}$

Fig 10. Sub-threshold drain current as a function of gate-source voltage



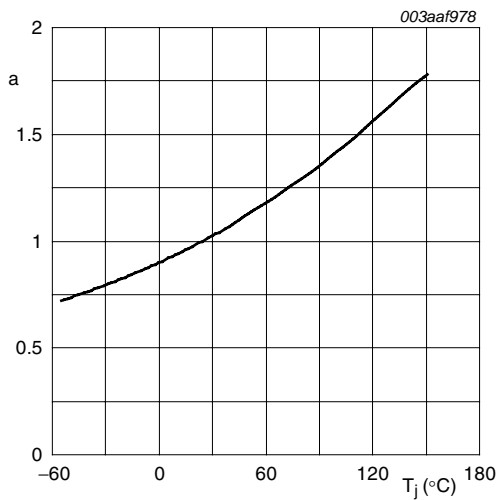
$I_D = 1 \text{ mA}; V_{DS} = V_{GS}$

Fig 11. Gate-source threshold voltage as a function of junction temperature



$T_j = 25^\circ\text{C}$

Fig 12. Drain-source on-state resistance as a function of drain current; typical values



$$a = \frac{R_{DS(on)}}{R_{DS(on)25^\circ\text{C}}}$$

Fig 13. Normalized drain-source on-state resistance factor as a function of junction temperature

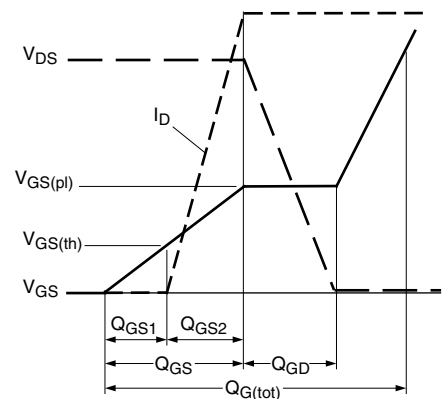
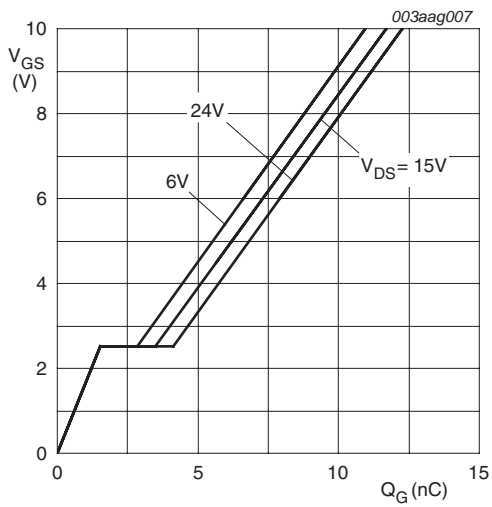
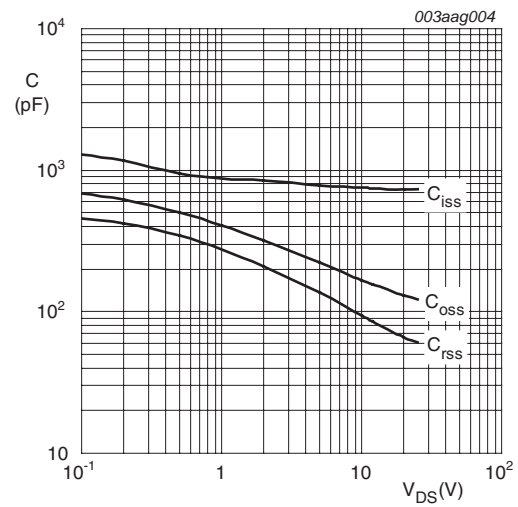


Fig 14. Gate charge waveform definitions



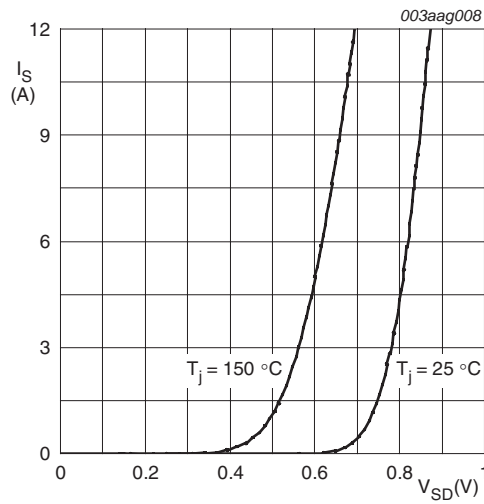
$T_j = 25^\circ\text{C}$ and $I_D = 5\text{A}$

Fig 15. Gate-source voltage as a function of gate charge; typical values



$V_{GS} = 0\text{ V}$, $f = 1\text{ MHz}$

Fig 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values



$V_{GS} = 0\text{ V}$

Fig 17. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

7. Package outline

SO8: plastic small outline package; 8 leads; body width 3.9 mm

SOT96-1

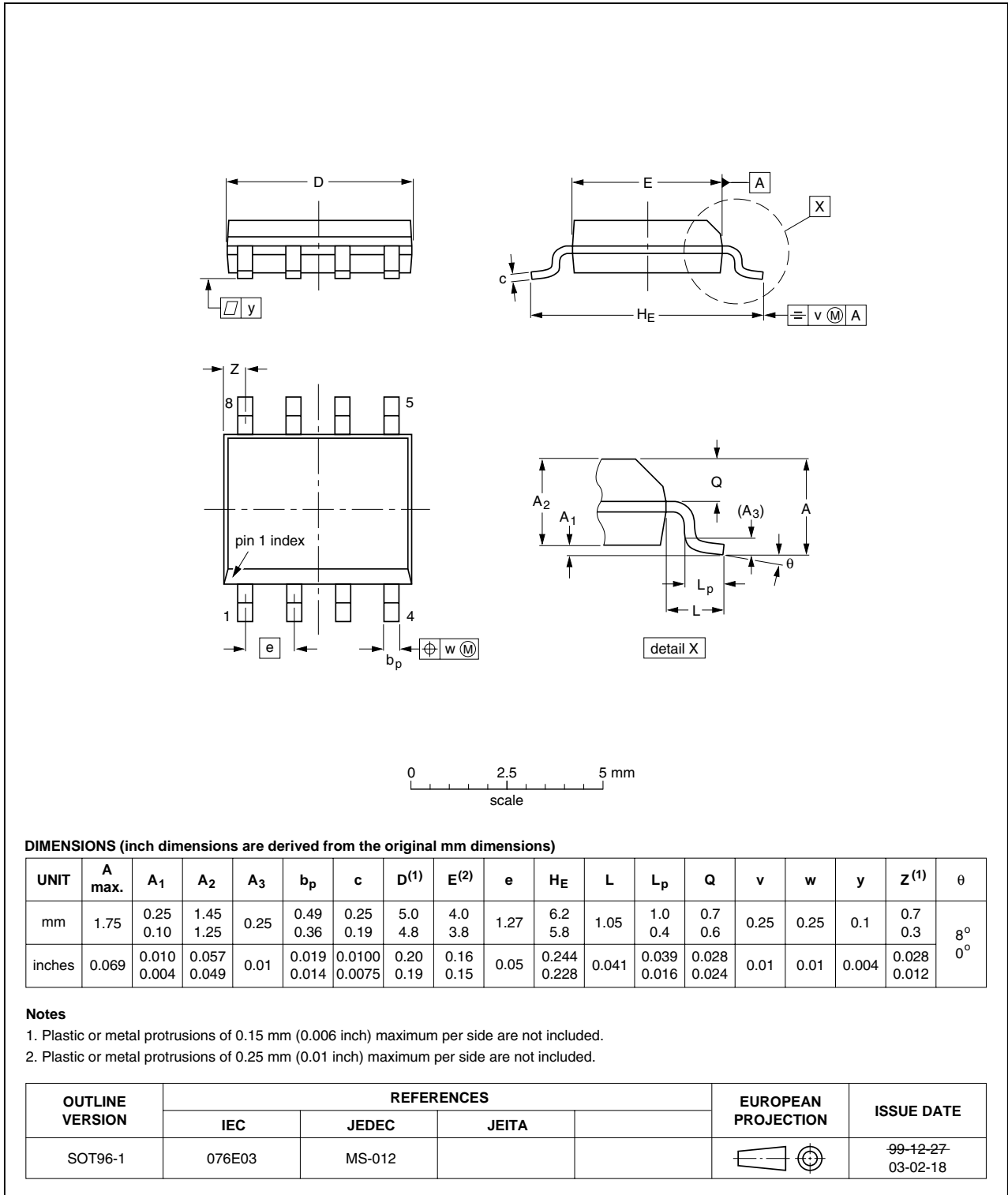


Fig 18. Package outline SOT96-1 (SO8)

8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN013-30KL v.1	20110414	Objective data sheet	-	-

9. Legal information

9.1 Data sheet status

Document status ^[1] ^[2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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